

RF Power MOSFET Transistor 40 W, 2 - 175 MHz, 28 V

Rev. V1

Features

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- · High saturated output power
- Lower noise figure than bipolar devices
- RoHS Compliant

ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V _{GS}	20	V
Drain-Source Current	I _{DS}	8	Α
Power Dissipation	P _D	125	W
Junction Temperature	TJ	200	°C
Storage Temperature	T _{STG}	-55 to +150	°C
Thermal Resistance	θ _{JC}	1.4	°C/W

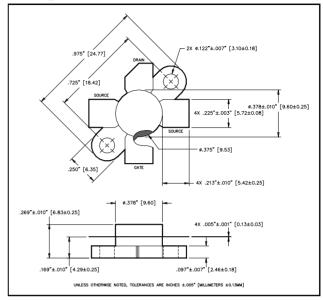
TYPICAL DEVICE IMPEDANCE

F (MHz)	Z _{IN} (Ω)	Z _{LOAD} (Ω)		
30	12.0 - j6.8	6.5 - j1.5		
50	10.0 - j6.5	6.0 - j1.8		
100	6.0 - j5.5	5.5 - j1.8		
200 1.1 - j3.0 3.5 - j1.8				
$V_{DD} = 28V$, $I_{DQ} = 200$ mA, $P_{OUT} = 40$ W				

 Z_{IN} is the series equivalent input impedance of the device from gate to source.

 $Z_{\text{\tiny LOAD}}$ is the optimum series equivalent load impedance as measured from drain to ground.

Package Outline



LETTER	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
А	24.64	24.89	.970	.980
В	18.29	18.54	.720	.730
С	20.07	20.83	.790	.820
D	9.47	9.73	.373	.383
Е	6.22	6.48	.245	.255
F	5.64	5.79	.222	.228
G	2.92	3.30	.115	.130
Н	2.29	2.67	.090	.105
J	4.04	4.55	.159	.179
К	6.58	7.39	.259	.291
L	.10	.15	.004	.006

ELECTRICAL CHARACTERISTICS AT 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	65	-	V	V _{GS} = 0.0 V , I _{DS} = 10.0 mA
Drain-Source Leakage Current	I _{DSS}	-	2.0	mA	V _{GS} = 28.0 V , V _{GS} = 0.0 V
Gate-Source Leakage Current	I _{GSS}	-	2.0	μA	V _{GS} = 20.0 V , V _{DS} = 0.0 V
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	V _{DS} = 10.0 V , I _{DS} = 200.0 mA
Forward Transconductance	G_{M}	1	-	S	V_{DS} = 10.0 V , I_{DS} = 2000.0 mA , Δ V_{GS} = 1.0V, 80 μ s Pulse
Input Capacitance	C _{ISS}	-	90	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Output Capacitance	Coss	-	80	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C _{RSS}	-	16	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Power Gain	G _P	13	-	dB	V_{DD} = 28.0 V, I_{DQ} = 200 mA, P_{OUT} = 40 W F =175 MHz
Drain Efficiency	ŋ _D	60	-	%	V_{DD} = 28.0 V, I_{DQ} = 200 mA, P_{OUT} = 40 W F =175 MHz
Load Mismatch Tolerance	VSWR-T	-	30:1	-	V_{DD} = 28.0 V, I_{DQ} = 200 mA, P_{OUT} = 40 W F =175 MHz

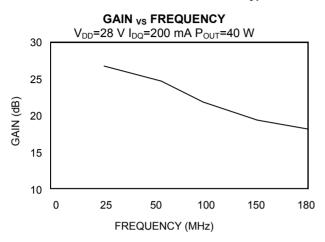
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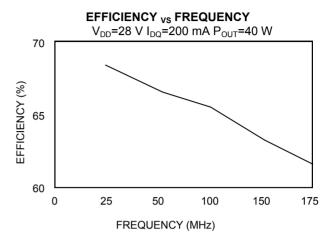


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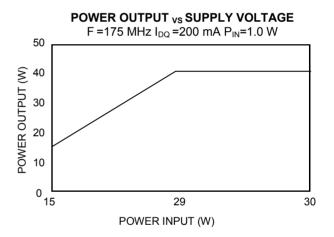
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Typical Broadband Performance Curves





POWER OUTPUT _{VS} POWER INPUT $V_{DD} = 28 \text{ V } I_{DQ} = 100 \text{ mA}$ 60 50 100MHz POWER OUTPUT (W) 175MHz 40 30 20 10 0 0.5 0.1 0.5 1 1.5 0.3 POWER INPUT (W)

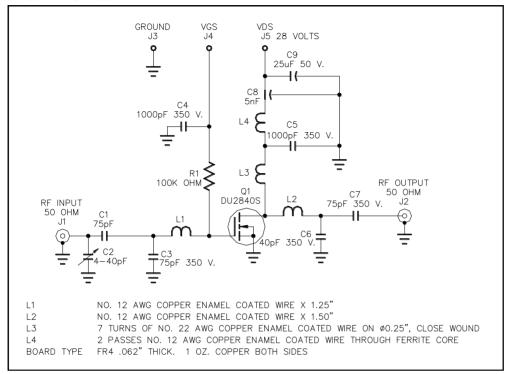




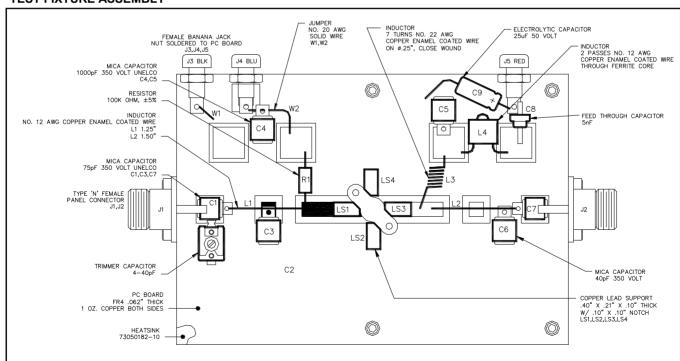
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TEST FIXTURE SCHEMATIC



TEST FIXTURE ASSEMBLY



DU2840S



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